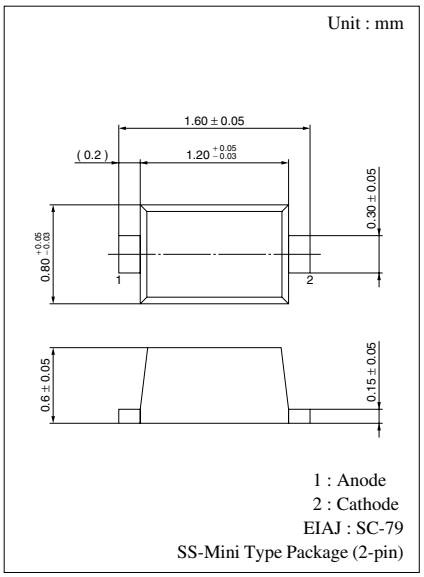
MA2S111

Silicon epitaxial planar type

For switching circuits



Marking Symbol: A

■ Features

- Super-small SS-mini type package
- Allowing high-density mounting
- Short reverse recovery time t_{rr}
- Small terminal capacitance, C_t

■ Absolute Maximum Ratings $T_a = 25°C$

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	80	V
Peak reverse voltage	V_{RM}	80	V
Average forward current	$I_{F(AV)}$	100	mA
Peak forward current	I_{FM}	225	mA
Non-repetitive peak forward surge current*	I_{FSM}	500	mA
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	−55 to +150	°C

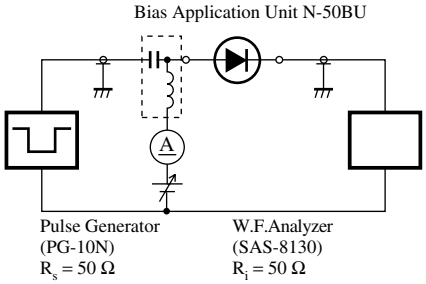
Note) * : t = 1 s

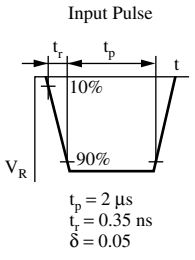
■ Electrical Characteristics $T_a = 25°C$

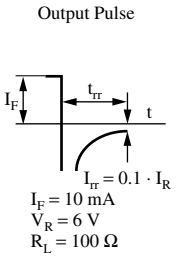
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	I_R	V_R = 75 V			100	nA
Forward voltage (DC)	V_F	I_F = 100 mA		0.95	1.2	V
Reverse voltage (DC)	V_R	I_R =100 µA	80			V
Terminal capacitance	C_t	V_R = 0 V, f = 1 MHz		0.6	2	pF
Reverse recovery time*	t_{rr}	I_F = 10 mA, V_R = 6 V I_{rr} = 0.1 · I_R, R_L = 100 Ω			3	ns

Note) 1. Rated input/output frequency: 100 MHz

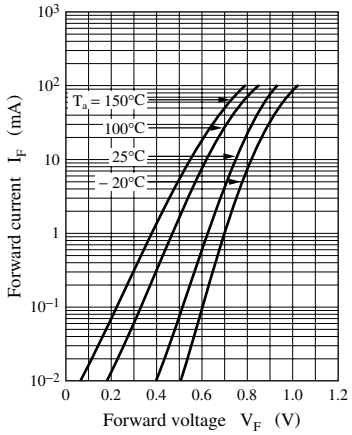
2. * : t_{rr} measuring circuit



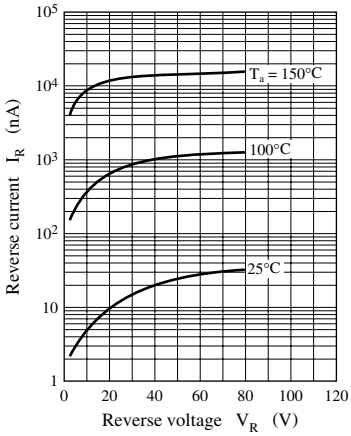




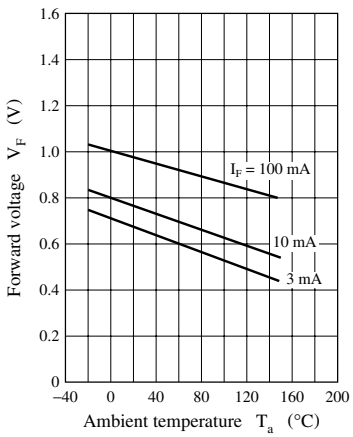
I_F — V_F



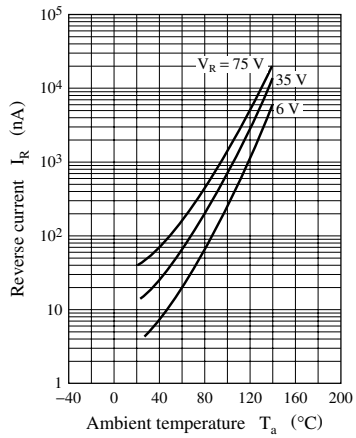
I_R — V_R



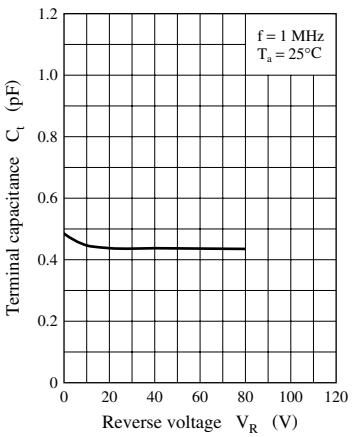
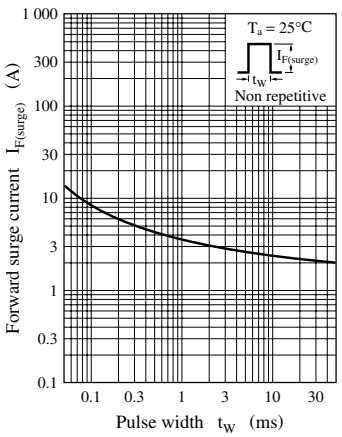
V_F — T_a



I_R — T_a



C_t — V_R



$I_{F(surge)}$ — t_W